Microwave Transistors, Continuous Power (cont.)

Type No.	Package Outline	f (GHz)	V_{CE} (V)	I_C (mA)	P_{L1}(1) (W)	G_{PO}(2) (dB)
CLASS A, MEDIUM POWER (cont.)						
LAE4001R	SOT-100	4.0	15	25	.085	9.5
LAE4002S	SOT-100	4.0	18	30	.126	8
LTE4002S	FO-41B	4.0	18	30	.200 typ	8
LTE42005S	FO-41B	4.2	18	110	.550	7.2
LTE42008R	FO-41B	4.2	16	250	.940	7.5
LTE42012R	FO-41B	4.2	16	400	1.250	7
CLASS A, HIGH POWER						
LZ1418E100R	FO-57C	1.4 - 1.8	16	2	9	10
LV1721E50R	FO-83	1.7 - 2.1	16	1.1	5	7
LV2024E45R	FO-83	2.0 - 2.4	16	1.1	4	6
LVE21050R	FO-83	2.1	16	1.1	5.5 typ	8 typ
LV2327E40R	FO-83	2.3 - 2.7	16	1	4	7
LV2931E50R	FO-83B	2.9 - 3.1	16	1	4.5	6
CLASS AB						
LLE18010X	FO-229	1.85	24	10	1.5	10
LLE16045X	FO-229	1.65	24	50	5.0	10
LLE18040X	FO-229	1.85	24	50	4.5	10
LLE16120X	FO-229	1.65	24	100	11	10
LLE18100X	FO-229	1.85	24	100	13	10.8
LLE16350X	FO-229	1.65	24	100	35	8
LLE18300X	FO-229	1.85	24	100	30	9
LXE16350X	FO-91	1.65	24	300	35	10
LXE18300X	FO-91	1.85	24	300	30	9

(1) Load power for 1 dB compressed power gain. (2) Low-level power gain associated with P_{L1}.

Microwave Transistors, Continuous Power (cont.)

Type No.	Package Outline	f (GHz)	V_{CE} (V)	P_L (W)	Gp (dB)	η_C (%)
CLASS B, MEDIUM POWER						
PLB16004U	FO-229	1.65	28	4	10	45
PTB23001X	FO-41B	2	24	1	7	45
PTB23002U	FO-41B	2.3	28	2	9	45
PTB23003X	FO-41B	2	24	3	8.75	45
PTB23005X	FO-41B	2	24	5	9.2	50
PTB32001X	FO-41B	3	24	1.3	8	35
PTB32003X	FO-41B	3	24	2.5	8	35
PTB32005X	FO-41B	3	24	4.5	8	35
PTB42001X	FO-41B	4.2	24	0.8	5	28
PTB42002X	FO-41B	4.2	24	1.6	5	28
PTB42003X	FO-41B	4.2	24	2.5	5	28
PVB42004X	FO-83	1	24	13	11	60
		2	24	10	10	48
		3	24	7.5	8.8	30
		4	24	4	6	25
CLASS B, HIGH POWER						
PZ1418B15U	FO-57C	1.4 - 1.8	28	12.5	7	38
PZ1418B30U	FO-57C	1.4 - 1.8	28	27	7.3	38

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